

WHAT IS CLAIMED IS:

Sub A'7

1. An alignment mark configuration, which is applicable on a substrate comprising a plurality of layers, the alignment mark configuration comprising:

5 an alignment mark on the substrate, wherein the alignment mark comprises a plurality of recesses and a spacing between the neighboring recesses is "d"; and

a trench, wherein a spacing between the trench and the alignment mark is in a range between about 5d to 80d.

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Sub B'7

2. The alignment mark configuration according to claim 1, wherein the recesses include a plurality of trenches formed by a shallow trench isolation fabrication process.

3. The alignment mark configuration according to claim 1, wherein the trench includes a shallow trench isolation structure.